

High voltage fast-switching NPN power transistor

Features

- High voltage capability
- Low spread of dynamic parameters
- Minimum lot-to-lot spread for reliable operation
- Very high switching speed

Applications

- Compact fluorescent lamps (CFLS)
- SMPS for battery charger

Description

The device is manufactured using high voltage multi epitaxial planar technology for high switching speeds and high voltage capability. It uses a cellular emitter structure with planar edge termination to enhance switching speeds while maintaining the wide RBSOA.

The STBV32G and STBV32G-AP are supplied using halogen-free molding compound.

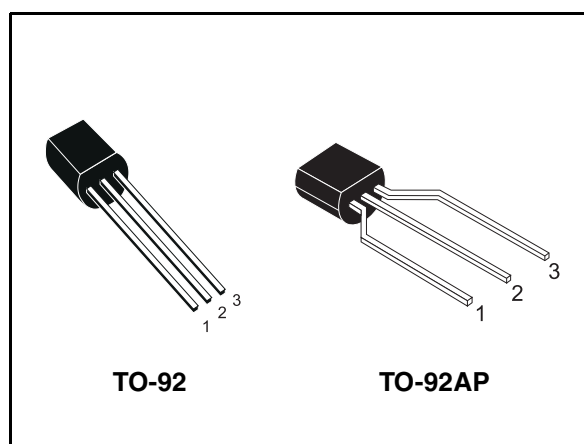


Figure 1. Internal schematic diagram

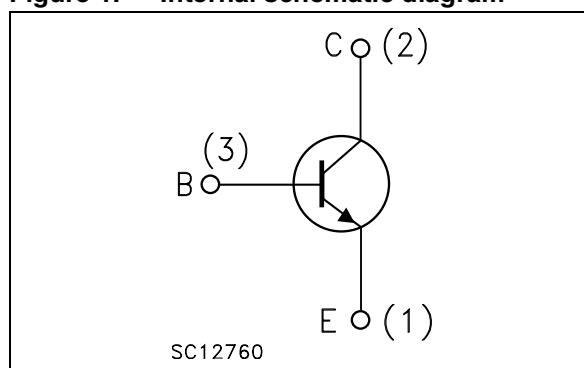


Table 1. Device summary

Order codes	Marking	Package	Packaging
STBV32	BV32	TO-92	Bulk
STBV32G	BV32G	TO-92	Bulk
STBV32-AP	BV32	TO-92AP	Ammopack
STBV32G-AP	BV32G	TO-92AP	Ammopack

1 Electrical ratings

Table 2. Absolute maximum rating

Symbol	Parameter	Value	Unit
V_{CES}	Collector-emitter voltage ($V_{BE} = 0$)	700	V
V_{CEO}	Collector-emitter voltage ($I_B = 0$)	400	V
V_{EBO}	Collector-base voltage ($I_C = 0$, $I_B = 0.5A$, $t_P < 10$ ms)	$V_{(BR)EBO}$	V
I_C	Collector current ($f \geq 100$ Hz, duty-cycle $\leq 50\%$, $T_C = 25$ °C)	1.5	A
I_{CM}	Collector peak current ($t_P < 5$ ms)	3	A
I_B	Base current	0.5	A
I_{BM}	Base peak current ($t_P < 5$ ms)	1.5	A
P_{TOT}	Total dissipation at $T_C = 25$ °C	1.5	W
T_{stg}	Storage temperature	-65 to 150	°C
T_J	Max. operating junction temperature	150	

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case max	83.3	°C/W

2 Electrical characteristics

($T_{\text{case}} = 25\text{ °C}$; unless otherwise specified)

Table 4. Electrical characteristics

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{CES}	Collector cut-off current ($V_{\text{BE}} = 0$)	$V_{\text{CE}} = 700\text{ V}$			1	mA
		$V_{\text{CE}} = 700\text{ V}$ $T_{\text{C}} = 125\text{ °C}$			5	mA
$V_{(\text{BR})\text{EBO}}$	Emitter-base breakdown voltage ($I_{\text{C}} = 0$)	$I_{\text{E}} = 10\text{ mA}$	9		18	V
$V_{\text{CEO(sus)}}^{(1)}$	Collector-emitter sustaining voltage ($I_{\text{B}} = 0$)	$I_{\text{C}} = 10\text{ mA}$	400			V
$V_{\text{CE(sat)}}^{(1)}$	Collector-emitter saturation voltage	$I_{\text{C}} = 0.5\text{ A}$ $I_{\text{B}} = 100\text{ mA}$			0.5	V
		$I_{\text{C}} = 1\text{ A}$ $I_{\text{B}} = 250\text{ mA}$			1	V
		$I_{\text{C}} = 1.5\text{ A}$ $I_{\text{B}} = 500\text{ mA}$			1.5	V
$V_{\text{BE(sat)}}^{(1)}$	Base-emitter saturation voltage	$I_{\text{C}} = 0.5\text{ A}$ $I_{\text{B}} = 100\text{ mA}$			1	V
		$I_{\text{C}} = 1\text{ A}$ $I_{\text{B}} = 250\text{ mA}$			1.2	V
h_{FE}	DC current gain	$I_{\text{C}} = 0.5\text{ mA}$ $V_{\text{CE}} = 2\text{ V}$	20			
		$I_{\text{C}} = 0.5\text{ A}$ $V_{\text{CE}} = 2\text{ V}$	8		25	
		$I_{\text{C}} = 1\text{ A}$ $V_{\text{CE}} = 2\text{ V}$	5		25	
t_{r} t_{s} t_{f}	Resistive load Rise time Storage time Fall time	$I_{\text{C}} = 1\text{ A}$ $t_{\text{p}} = 25\text{ }\mu\text{s}$			1	μs
		$I_{\text{B1}} = -I_{\text{B2}} = 200\text{ mA}$			4	μs
		$V_{\text{CC}} = 125\text{ V}$ <i>Figure 12.</i>			0.7	μs
t_{s}	Inductive Load Storage time	$I_{\text{C}} = 1\text{ A}$ $V_{\text{clamp}} = 300\text{ V}$ $I_{\text{B1}} = 200\text{ mA}$ $V_{\text{BE(off)}} = -5\text{ V}$ $L = 50\text{ mH}$ $R_{\text{BB}} = 0$ <i>Figure 13.</i>		0.8		μs

1. Pulsed duration = 300 μs , duty cycle $\leq 1.5\%$

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

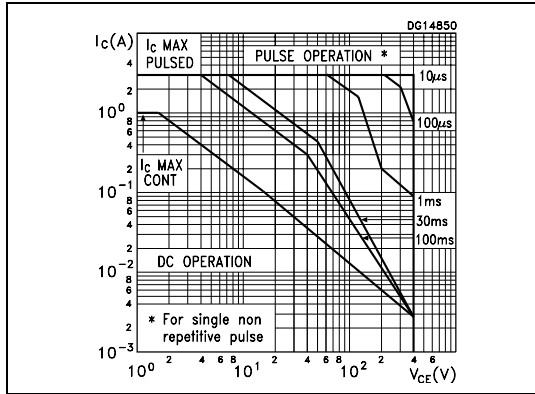


Figure 3. Derating curve

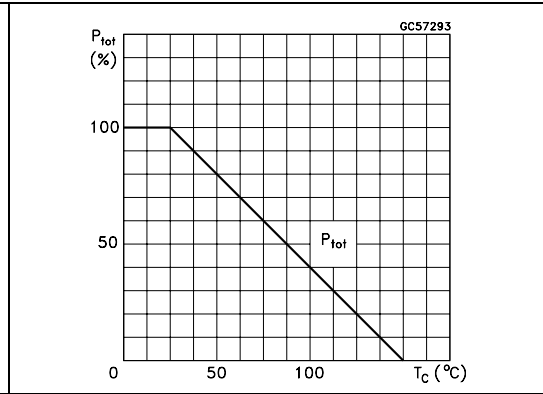


Figure 4. Output characteristics

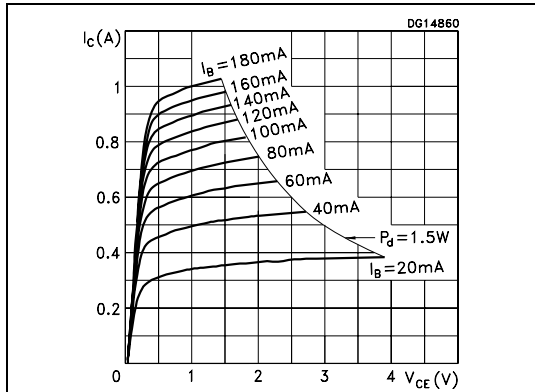


Figure 5. Reverse biased safe operating area

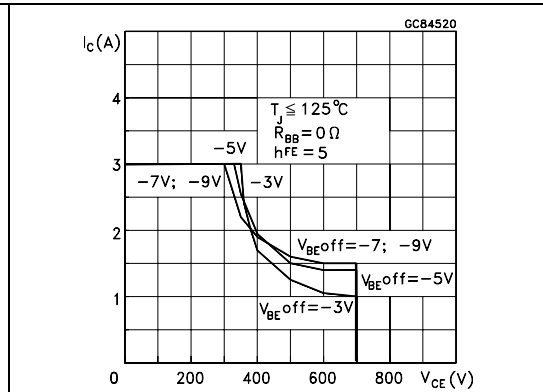


Figure 6. DC current gain

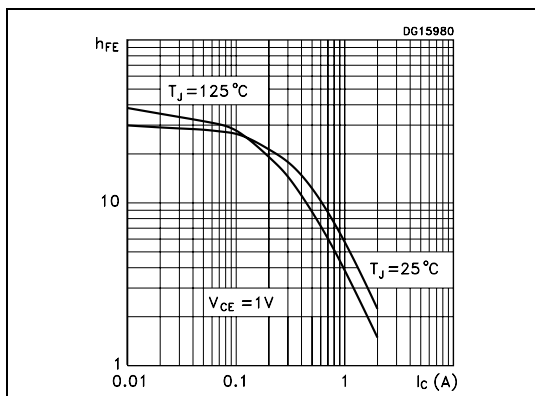


Figure 7. DC current gain

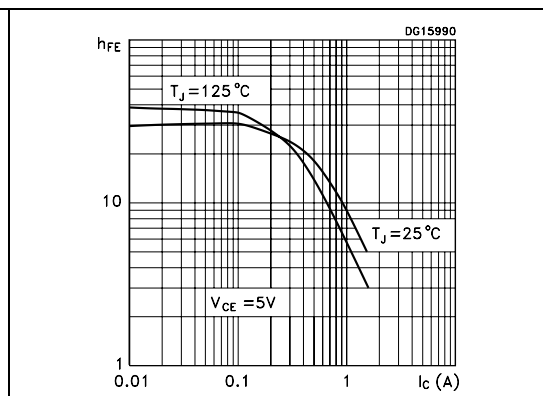


Figure 8. Collector-emitter saturation voltage

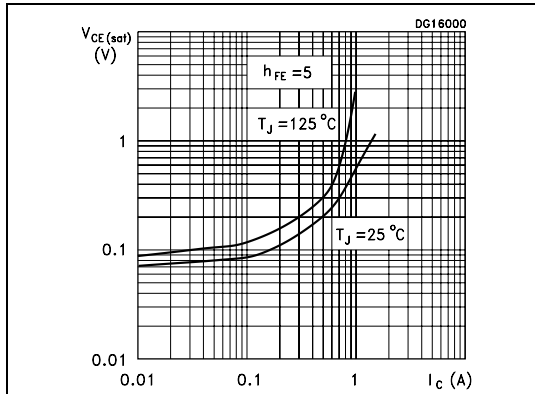


Figure 9. Base-emitter saturation voltage

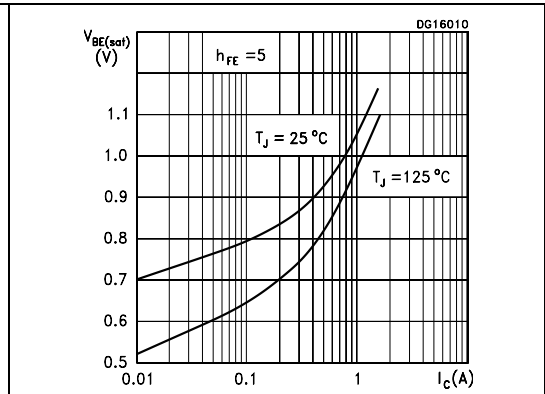


Figure 10. Inductive load switching time

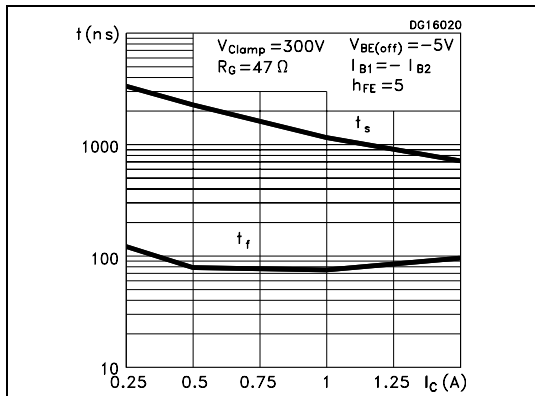
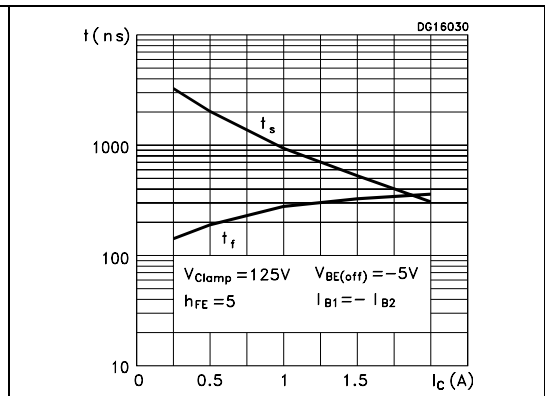


Figure 11. Resistive load switching time



2.2 Test circuits

Figure 12. Resistive load switching test circuit

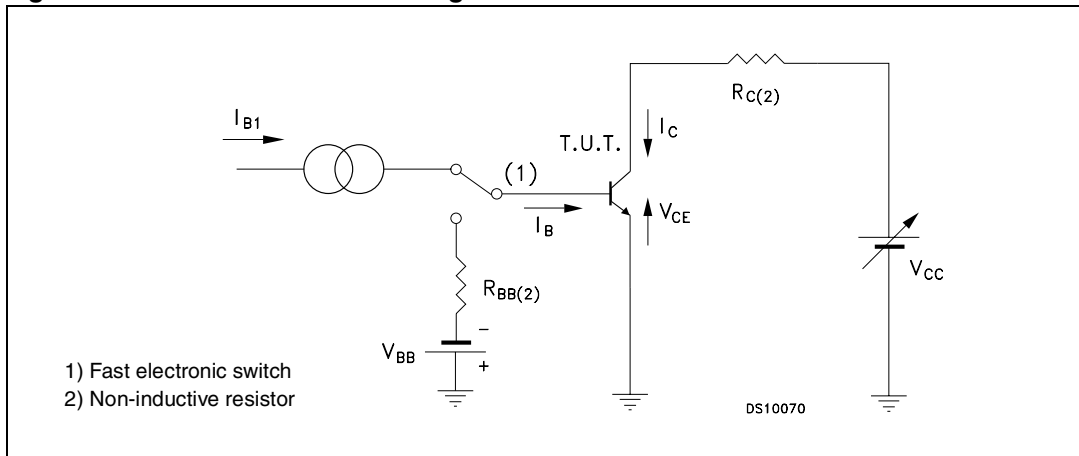
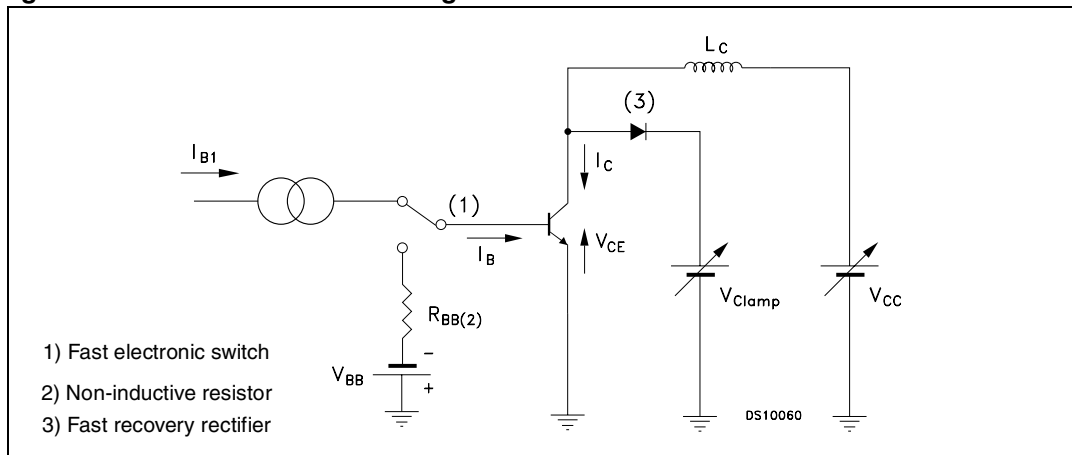


Figure 13. Inductive load switching test circuit

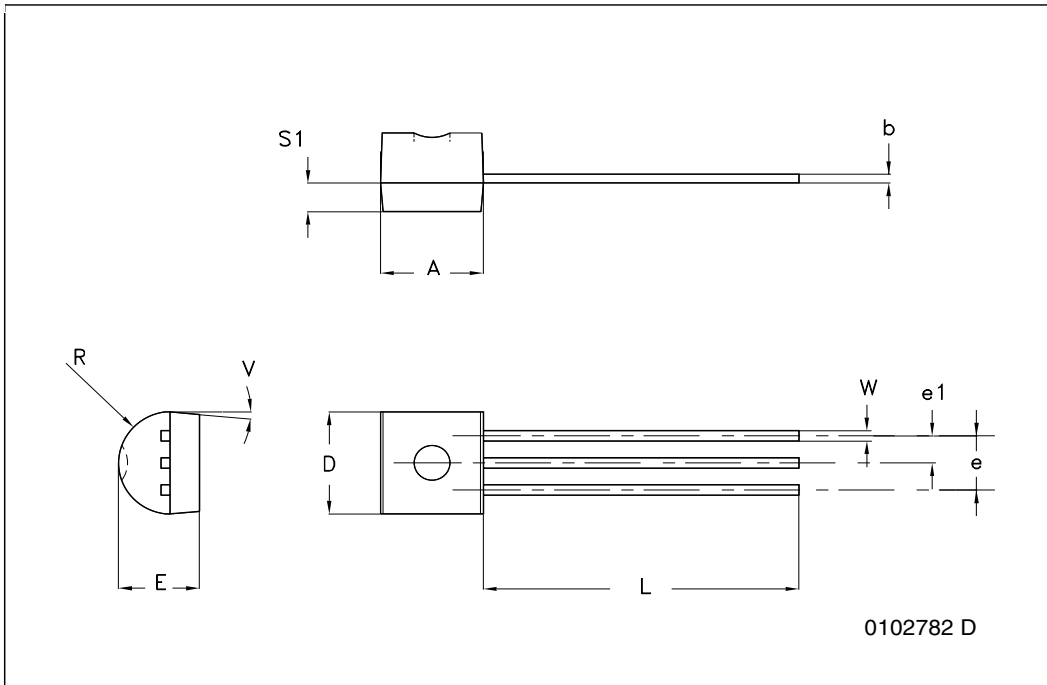


3 Package mechanical data

In order to meet environmental requirements, ST offers these devices in ECOPACK® packages. These packages have a Lead-free second level interconnect . The category of second level interconnect is marked on the package and on the inner box label, in compliance with JEDEC Standard JESD97. The maximum ratings related to soldering conditions are also marked on the inner box label. ECOPACK is an ST trademark. ECOPACK specifications are available at: www.st.com

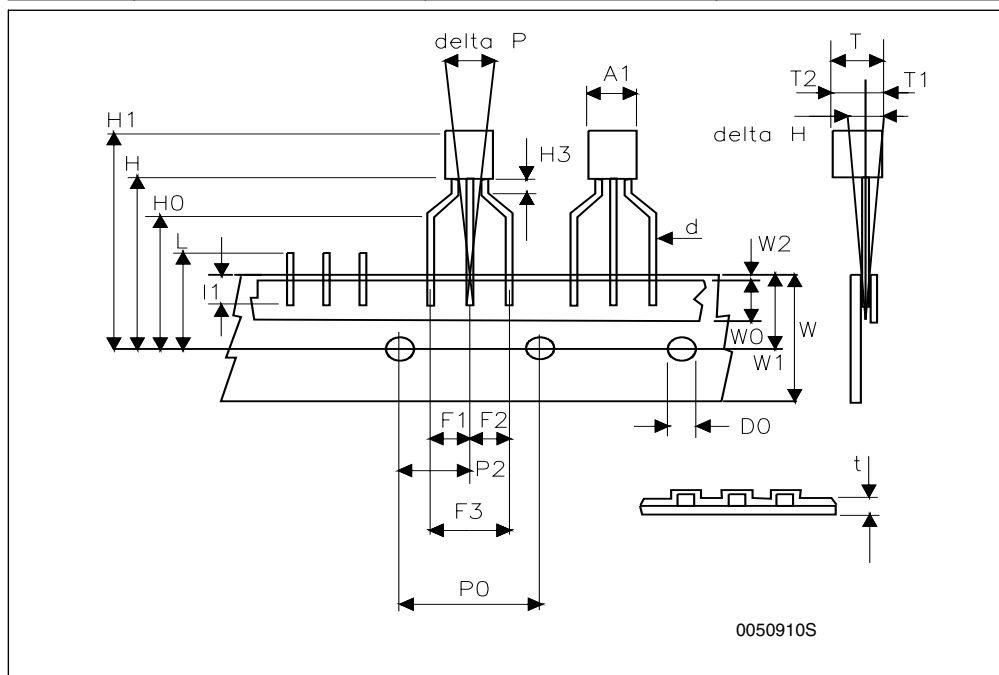
TO-92 bulk shipment mechanical data

DIM.	mm.		
	MIN.	TYP	MAX.
A	4.32		4.95
b	0.36		0.51
D	4.45		4.95
E	3.30		3.94
e	2.41		2.67
e1	1.14		1.40
L	12.70		15.49
R	2.16		2.41
S1	0.92		1.52
W	0.41		0.56
V		5°	



TO-92 ammopack shipment (suffix"-AP") mechanical data

Dim.	mm		
	Min	Typ	Max
A1			4.80
T			3.80
T1			1.60
T2			2.30
d			0.48
P0	12.50	12.70	12.90
P2	5.65	6.35	7.05
F1,F2	2.44	2.54	2.94
F3	4.98	5.08	5.48
delta H	-2.00		2.00
W	17.50	18.00	19.00
W0	5.70	6.00	6.30
W1	8.50	9.00	9.25
W2			0.50
H	18.50		20.50
H3	0.5	1	1.5
H0	15.50	16.00	16.50
H1			25.00
D0	3.80	4.00	4.20
t			0.90
L			11.00
I1	3.00		
delta P	-1.00		1.00



4 Revision history

Table 5. Document revision history

Date	Revision	Changes
02-Jul-2008	8	Added halogen-free molding compound package.

Please Read Carefully:

Information in this document is provided solely in connection with ST products. STMicroelectronics NV and its subsidiaries ("ST") reserve the right to make changes, corrections, modifications or improvements, to this document, and the products and services described herein at any time, without notice.

All ST products are sold pursuant to ST's terms and conditions of sale.

Purchasers are solely responsible for the choice, selection and use of the ST products and services described herein, and ST assumes no liability whatsoever relating to the choice, selection or use of the ST products and services described herein.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted under this document. If any part of this document refers to any third party products or services it shall not be deemed a license grant by ST for the use of such third party products or services, or any intellectual property contained therein or considered as a warranty covering the use in any manner whatsoever of such third party products or services or any intellectual property contained therein.

UNLESS OTHERWISE SET FORTH IN ST'S TERMS AND CONDITIONS OF SALE ST DISCLAIMS ANY EXPRESS OR IMPLIED WARRANTY WITH RESPECT TO THE USE AND/OR SALE OF ST PRODUCTS INCLUDING WITHOUT LIMITATION IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE (AND THEIR EQUIVALENTS UNDER THE LAWS OF ANY JURISDICTION), OR INFRINGEMENT OF ANY PATENT, COPYRIGHT OR OTHER INTELLECTUAL PROPERTY RIGHT.

UNLESS EXPRESSLY APPROVED IN WRITING BY AN AUTHORIZED ST REPRESENTATIVE, ST PRODUCTS ARE NOT RECOMMENDED, AUTHORIZED OR WARRANTED FOR USE IN MILITARY, AIR CRAFT, SPACE, LIFE SAVING, OR LIFE SUSTAINING APPLICATIONS, NOR IN PRODUCTS OR SYSTEMS WHERE FAILURE OR MALFUNCTION MAY RESULT IN PERSONAL INJURY, DEATH, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE. ST PRODUCTS WHICH ARE NOT SPECIFIED AS "AUTOMOTIVE GRADE" MAY ONLY BE USED IN AUTOMOTIVE APPLICATIONS AT USER'S OWN RISK.

Resale of ST products with provisions different from the statements and/or technical features set forth in this document shall immediately void any warranty granted by ST for the ST product or service described herein and shall not create or extend in any manner whatsoever, any liability of ST.

ST and the ST logo are trademarks or registered trademarks of ST in various countries.

Information in this document supersedes and replaces all information previously supplied.

The ST logo is a registered trademark of STMicroelectronics. All other names are the property of their respective owners.

© 2008 STMicroelectronics - All rights reserved

STMicroelectronics group of companies

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States of America

www.st.com

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for [RF Bipolar Transistors](#) category:

Click to view products by [STMicroelectronics](#) manufacturer:

Other Similar products are found below :

[MAPRST0912-50](#) [MCH4016-TL-H](#) [MMBT5551-G](#) [PH3135-90S](#) [MRF10120](#) [MRF587](#) [15GN01CA-TB-E](#) [BFR 360L3 E6765](#) [PH1214-25M](#)
[2SA1257-5-TB-E](#) [MAPRST0912-350](#) [MCH4014-TL-H](#) [MMBTH10-TP](#) [BFP 620F H7764](#) [BFP 640F H6327](#) [BFP 720F H6327](#) [BFP 740F](#)
[H6327](#) [BFR 340L3 E6327](#) [BFR 360F H6765](#) [BFR 740L3RH E6327](#) [PH2729-25M](#) [MRF10031](#) [NSVF4009SG4T1G](#) [DSC5G02D0L](#) [BFP](#)
[182R E7764](#) [BFP405H6740XTSA1](#) [MRF10350](#) [MRF321](#) [PH2729-65M](#) [MRF317](#) [ASMA201](#) [MCH4015-TL-H](#) [BF888H6327XTSA1](#)
[MMBT2222A-G](#) [BFP196WH6327XTSA1](#) [BFP405FH6327XTSA1](#) [BFP640ESDH6327XTSA1](#) [BFR193L3E6327XTMA1](#) [BFU550WX](#)
[BFU550XRR](#) [BFU580QX](#) [NSVF4020SG4T1G](#) [NSVF6003SB6T1G](#) [MMBT5179](#) [MS1406](#) [STBV32-AP](#) [MRF10005](#) [BFG520,215](#)
[BFP740FESDH6327XTSA1](#) [BFP 842ESD H6327](#)